OPB703 through OPB705, OPB703WZ through OPB705WZ, OPB70AWZ, OPB70DWZ, OPB70EWZ, OPB70FWZ Obsolete (OPB70BWZ, OPB70CWZ, OPB70HWZ, OPB704G)

Features:

- Phototransistor output
- High sensitivity
- Low-cost plastic housing
- Available with lenses for dust protection and ambient light filtration
- Focused for maximum sensitivity

Description:

- The **OPB703**, **OPB704** and **OPB705** consist of an Infrared (890 nm) Light Emitting Diode (LED) and a NPN silicon Phototransistor, mounted side-by-side on converging optical axes in a black plastic housing and are designed for PCBoard mounting. The **OPB703WZ**, **OPB704WZ** and **OPB705WZ** are designed for remote mounting utilizing interconnect wires of UL approved 26 AWG, 24" (61.0 cm) minimum length, stripped and tinned.
- The **OPB70AWZ** consists of an Infrared (890 nm) Light Emitting Diode (LED) and a NPN silicon Photodarlington, mounted side-byside on converging optical axes in a black plastic housing and is designed for remote mounting utilizing interconnect wires of UL approved 26 AWG, 24" (61.0 cm) minimum length, stripped and tinned.
- The **OPB70DWZ through OPB70FWZ** consist of a Visible (Red 660 nm) Light Emitting Diode (LED) and a NPN silicon Phototransistor or Rbe Phototransistor, mounted side-by-side on converging optical axes in a black plastic housing and are designed for remote mounting utilizing interconnect wires of UL approved 26 AWG, 24" (61.0 cm) minimum length, stripped and tinned.
- Various lens options are available: No lens for the (OPB703, OPB703WZ), blue window for dust protection for the (OPB704, OPB704WZ) and aperture lens for improved resolution for the (OPB705, OPB705WZ, OPB70AWZ, OPB70DWZ). The OPB704GWZ offers excellent protection for dirty environments.
- The phototransistor responds to illumination from the emitter when a reflective object passes within the field of view centered typically at 0.15" (3.8 mm).

Custom electrical, wire, cabling and connectors are available. Contact your local representative or OPTEK for more information.

Applications:

- Non-contact reflective object sensor
- Assembly line automation
- Machine automation
- Machine safety
- End of travel sensor
- Door sensor
- Mark Detection
- Office Equipment
- Gaming Equipment

Ordering information									
Part	LED Peak	Detector	Optical Cover	Lead or Wire					
OPB703			0.160" Leads						
OPB703WZ			None	24" / 26 AWG Wire					
OPB704]			0.160" Leads					
OPB704WZ				24" / 26 AWG Wire					
OPB70HWZ (Obsolete)		Transistor Blue 24" / 2 Window	24" / 26 AWG Wire						
OPB704G (Obsolete)	890 nm		Window	0.160" Leads					
OPB704GWZ				24" / 26 AWG Wire					
OPB705				0.160" Leads					
OPB705WZ			Aperture						
OPB70AWZ		Darlington							
OPB70BWZ (Obsolete)		Rbe Transistor	Blue Window						
OPB70CWZ (Obsolete)		Rbe Transistor	Aperture	24" / 26 AWG Wire					
OPB70DWZ	660 nm	Transistor							
OPB70EWZ]	Rbe Transistor	Clear Window						
OPB70FWZ		Transistor	Clear Window						

Ordering Information

General Note

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OPB703 through OPB705, OPB703WZ through OPB705WZ, OPB70AWZ, OPB70DWZ, OPB70EWZ, OPB70FWZ Obsolete (OPB70BWZ, OPB70CWZ, OPB70HWZ, OPB704G)



OPB703, OPB704, OPB705

[5.1] [7] .275 R.063 .200 -REFLECTIVE SURFACE ₽ WIRE COLOR FUNCTION \bigcirc -0-ANODE CATHODE EMITTER [9.4] [17.8] ORANGE .700 \bigcirc -0-.370 GREEN - - -BLUE WHITE COLLECTOR К [5.6] .220 [3.8] .150 [10.7] NOM .420 [15.2] .600 [22.9] 900 DIMENSIONS ARE IN INCHES [MM] TOLERANCES ARE ± .010 UNLESS OTHERWISE SPECIFIED. Collector Anode Collector Collector Anode Anode Cathode Emitter Cathode Emitter Cathode Emitter

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Electronics

OPB703 through OPB705, OPB703WZ through OPB705WZ, OPB70AWZ, OPB70DWZ, OPB70EWZ, OPB70FWZ Obsolete (OPB70BWZ, OPB70CWZ, OPB70HWZ, OPB704G)

Electronics

OPB704GWZ



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OPB703 through OPB705, OPB703WZ through OPB705WZ, OPB70AWZ, OPB70DWZ, OPB70EWZ, OPB70FWZ Obsolete (OPB70BWZ, OPB70CWZ, OPB70HWZ, OPB704G)

Electrical Specifications

Absolute Maximum Ratings (T_A = 25° C unless otherwise noted)

Storage Temperature Range	-40° C to +80° C
Lead Soldering Temperature [1/16 inch (1.6 mm) from the case for 5 sec. with soldering iron]	240° C ⁽¹⁾
Input Diode	
Forward DC Current	40 mA
Reverse DC Voltage	2 V
Power Dissipation	100 mW ⁽²⁾
Output Photodetector	
Collector-Emitter Voltage Phototransistor Photodarlington	30 V 15 V
Emitter-Collector Voltage	5 V
Collector DC Current	25 mA
Power Dissipation	100 mW ⁽²⁾

Notes:

(1) RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.

(2) For OPB703WZ, OPB704WZ, OPB705WZ and OPB704GWZ derate linearly 1.82 mW/° C above 25° C.

General Note

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TT Electronics

OPB703 through OPB705, OPB703WZ through OPB705WZ, OPB70AWZ, OPB70DWZ, OPB70EWZ, OPB70FWZ Obsolete (OPB70BWZ, OPB70CWZ, OPB70HWZ, OPB704G)

Electrical Specifications

Electrical Characteristics (T_A = 25° C unless otherwise noted) (OPB703, OPB703WZ, OPB704, OPB704WZ, OPB705, OPB705WZ, OPB704GWZ)

SYMBOL	PARAMETER	MIN	ТҮР	МАХ	UNITS	TEST CONDITIONS		
Input Diod	e							
V _F	Forward Voltage	-	-	1.7	V	I _F = 40 mA		
I _R	Reverse Current	-	-	100	μΑ	V _R = 2 V		
Output Phototransistor								
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	30	-	-	V	I _{CE} = 100 μA		
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage	5	-	-	V	I _{EC} = 100 μA		
I _{CEO}	Collector Dark Current	-	-	250	nA	$V_{CE} = 10 \text{ V}, I_F = 0, E_E = 0$		
Coupled						·		
I _{C(ON)}	On-State Collector Current OPB703, OPB703WZ OPB704, OPB704WZ OPB705, OPB705WZ	0.30 0.20 0.15	- - -	2.5 2.5 1.0	mA	$V_{CE} = 5 \text{ V}, \text{ I}_{F} = 40 \text{ mA}, \text{ d} = 0.15'' $ ⁽⁴⁾⁽⁶⁾		
	OPB704GWZ	0.50	-	6.0		$V_{CE} = 5 \text{ V}, I_F = 40 \text{ mA}, d = 0.20''$ ⁽⁴⁾⁽⁶⁾		
I _{cx}	Crosstalk OPB703, OPB703WZ OPB704, OPB704WZ OPB705, OPB705WZ OPB704GWZ	- - -	- - -	20 20 10 100	μΑ	V _{CE} = 5 V, I _F = 40 mA ⁽⁵⁾		

Notes:

(1) RMA flux is recommended. Duration can be extended to 10 seconds maximum when flow soldering.

(2) For OPB703, OPB704 and OPB705, derate linearly 1.67 mW/° C above 25° C.

(3) For OPB703WZ, OPB704WZ, OPB705WZ, OPB706WZ, OPB70AWZ, OPB70DWZ, OPB70EWZ, and OPB70FWZ derate linearly 1.82 mW/° C above 25° C.

(4) The distance from the assembly face to the reflective surface is d.

(5) Crosstalk (I_{cx}) is the collector current measured with the indicated current in the input diode and with no reflecting surface.

(6) Measured using Eastman Kodak neutral white test card with 90 % diffuse reflectance as a reflecting surface. Reference: Eastman Kodak, Catalog # E 152 7795.

(7) All parameters tested using pulse techniques.

General Note

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OPB703 through OPB705, OPB703WZ through OPB705WZ, OPB70AWZ, OPB70DWZ, OPB70EWZ, OPB70FWZ Obsolete (OPB70BWZ, OPB70CWZ, OPB70HWZ, OPB704G)

Electrical Specifications

Electrical Characteristics (T_A = 25° C unless otherwise noted) (OPB70AWZ)

SYMBOL	PARAMETER	MIN	ТҮР	ΜΑΧ	UNITS	TEST CONDITIONS		
Input Diode								
V _F	Forward Voltage	-	-	1.7	V	I _F = 40 mA		
I _R	Reverse Current		-	100	μA	V _R = 2 V		
Output Pho	Output PhotoDarlington							
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	15	-	-	V	I _{CE} = 1.0 mA, E _E = 0		
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage	5	-	-	V	$I_{EC} = 100 \ \mu A, \ E_E = 0$		
I _{CEO}	Collector Dark Current	-	-	250	nA	$V_{CE} = 10 \text{ V}, \text{ I}_{F} = 0, \text{ E}_{E} = 0$		
Coupled	Coupled							
I _{C(ON)}	On-State Collector Current	5.0	-	26.0	mA	V_{CE} = 5 V, I _F = 40 mA, d = 0.15" ⁽¹⁾⁽³⁾		
V _(SAT)	Saturation Voltage	-	-	1.15	V	I_{CV} = 400 µA, I_F = 40 mA, d = 0.15" ⁽¹⁾⁽³⁾		
I _{cx}	Crosstalk	-	-	25	μA	V _{CE} = 5 V, I _F = 40 mA ⁽²⁾		

Notes:

(1) The distance from the assembly face to the reflective surface is d.

(2) Crosstalk (I_{CX}) is the collector current measured with the indicated current in the input diode and with no reflecting surface.

(3) Measured using Eastman Kodak neutral white test card with 90 % diffuse reflectance as a reflecting surface. Reference: Eastman Kodak, Catalog # E 152 7795.

General Note

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OPB703 through OPB705, OPB703WZ through OPB705WZ, OPB70AWZ, OPB70DWZ, OPB70EWZ, OPB70FWZ Obsolete (OPB70BWZ, OPB70CWZ, OPB70HWZ, OPB704G)

Electrical Specifications

Electrical Characteristics (T_A = 25° C unless otherwise noted) (OPB70EWZ)

SYMBOL	PARAMETER	MIN	ТҮР	МАХ	UNITS	TEST CONDITIONS		
Input Diode								
V _F	Forward Voltage	-	-	2.6	V	I _F = 40 mA		
I _R	Reverse Current	-	-	100	μΑ	V _R = 2 V		
Output Pho	Output Phototransistor							
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	30	-	-	V	$I_{CE} = 100 \ \mu A$, $I_F = 0$, $E_E = 0$		
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage	0.4	-	-	V	$I_{EC} = 100 \ \mu A$, $I_F = 0$, $E_E = 0$		
I _{CEO}	Collector Dark Current	-	-	100	nA	$V_{CE} = 10 V, I_F = 0, E_E = 0$		

Coupled

I _{C(ON)}	On-State Collector Current	OPB70EWZ	.25	-	2.5	mA	$V_{CE} = 5 \text{ V}, \text{ I}_{F} = 40 \text{ mA}, \text{ d} = 0.15'' (1)(3)$
V _(SAT)	Saturation Voltage		-	-	0.4	V	I_{c} = 100 µA, I_{F} = 40 mA, d = 0.15" ⁽¹⁾⁽³⁾
I _{CX}	Crosstalk		-	-	2	μΑ	$V_{CE} = 5 \text{ V}, I_F = 40 \text{ mA}^{(2)}$

Notes:

(1) The distance from the assembly face to the reflective surface is d.

(2) Crosstalk (I_{CX}) is the collector current measured with the indicated current in the input diode and with no reflecting surface.

(3) Measured using Eastman Kodak neutral white test card with 90 % diffuse reflectance as a reflecting surface. Reference: Eastman Kodak, Catalog # E 152 7795.

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OPB703 through OPB705, OPB703WZ through OPB705WZ, OPB70AWZ, OPB70DWZ, OPB70EWZ, OPB70FWZ Obsolete (OPB70BWZ, OPB70CWZ, OPB70HWZ, OPB704G)

Electrical Specifications

Electrical Characteristics (T_A = 25° C unless otherwise noted) (OPB70DWZ and OPB70FWZ)

SYMBOL	PARAMETER	MIN	ТҮР	МАХ	UNITS	TEST CONDITIONS		
Input Diode								
V_{F}	Forward Voltage	-	-	2.6	V	I _F = 40 mA		
I _R	Reverse Current		-	100	μΑ	V _R = 2 V		
Output Phototransistor								
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	30	-	-	V	$I_{CE} = 100 \ \mu A, I_F = 0, E_E = 0$		
V _{(BR)ECO}	Emitter-Collector Breakdown Voltage	5.0	-	-	V	$I_{EC} = 100 \ \mu A, \ I_F = 0, \ E_E = 0$		
I _{CEO}	Collector Dark Current	-	-	250	nA	$V_{CE} = 10 \text{ V}, \text{ I}_{\text{F}} = 0, \text{ E}_{\text{E}} = 0$		

Coupled

	On State Collector Current	OPB70DWZ	.10	-	1.5		V _{CE} = 5 V, I _F = 40 mA, d = 0.15" ⁽¹⁾⁽³⁾
IC(ON)	I _{C(ON)} On-State Collector Current	OPB70FWZ	.25	-	3.5	mA	$v_{CE} = 5 v$, $I_F = 40 \text{ IIIA}$, $u = 0.15$
V _(SAT)	Saturation Voltage		-	-	0.4	V	$I_{C(ON)}$ = 100 $\mu A,I_F$ = 40 mA, d = 0.15" $^{(1)(3)}$
I _{CX}	Crosstalk		-	-	5.0	μΑ	V _{CE} = 5 V, I _F = 40 mA ⁽²⁾

Notes:

(1) The distance from the assembly face to the reflective surface is d.

(2) Crosstalk (I_{cx}) is the collector current measured with the indicated current in the input diode and with no reflecting surface.

(3) Measured using Eastman Kodak neutral white test card with 90 % diffuse reflectance as a reflecting surface. Reference: Eastman Kodak, Catalog # E 152 7795.

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OPB703 through OPB705, OPB703WZ through OPB705WZ, OPB70AWZ, OPB70DWZ, OPB70EWZ, OPB70FWZ Obsolete (OPB70BWZ, OPB70CWZ, OPB70HWZ, OPB704G)



Performance

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Normalized Forward Current at 20 mA and 20° C 1.4 **Typical Forward Voltage** 1.2 1.0 40° C - -20° C 0° C 0.8 - 20° C 40° C - 60° C 80° C 0.6 0 5 10 15 20 25 30 35 40 Forward Current (mA)

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OPB704 - Output vs Distance

OPB703 through OPB705, OPB703WZ through OPB705WZ, OPB70AWZ, OPB70DWZ, OPB70EWZ, OPB70FWZ Obsolete (OPB70BWZ, OPB70CWZ, OPB70HWZ, OPB704G)



Performance

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